_M199/LM299/LM399/LM3999 Precision Reference

National Semiconductor

LM199/LM299/LM399/LM3999 Precision Reference

General Description

The LM199 series are precision, temperature-stabilized monolithic zeners offering temperature coefficients a factor of ten better than high quality reference zeners. Constructed on a single monolithic chip is a temperature stabilizer circuit and an active reference zener. The active circuitry reduces the dynamic impedance of the zener to about 0.5 Ω and allows the zener to operate over 0.5 mA to 10 mA current range with essentially no change in voltage or temperature coefficient. Further, a new subsurface zener structure gives low noise and excellent long term stability compared to ordinary monolithic zeners. The package is supplied with a thermal shield to minimize heater power and improve temperature ture regulation.

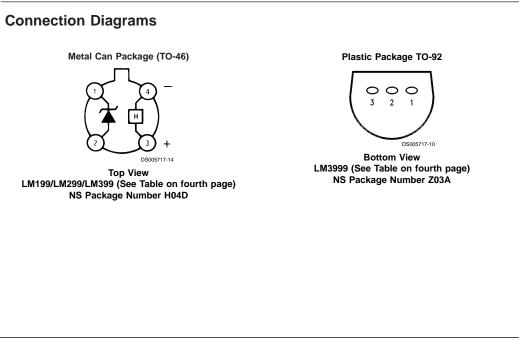
The LM199 series references are exceptionally easy to use and free of the problems that are often experienced with ordinary zeners. There is virtually no hysteresis in reference voltage with temperature cycling. Also, the LM199 is free of voltage shifts due to stress on the leads. Finally, since the unit is temperature stabilized, warm up time is fast.

The LM199 can be used in almost any application in place of ordinary zeners with improved performance. Some ideal applications are analog to digital converters, calibration standards, precision voltage or current sources or precision power supplies. Further in many cases the LM199 can replace references in existing equipment with a minimum of wiring changes. The LM199 series devices are packaged in a standard hermetic TO-46 package inside a thermal shield. The LM199 is rated for operation from -55° C to $+125^{\circ}$ C while the LM299 is rated for operation from -25° C to $+85^{\circ}$ C and the LM399 is rated from 0°C to $+70^{\circ}$ C.

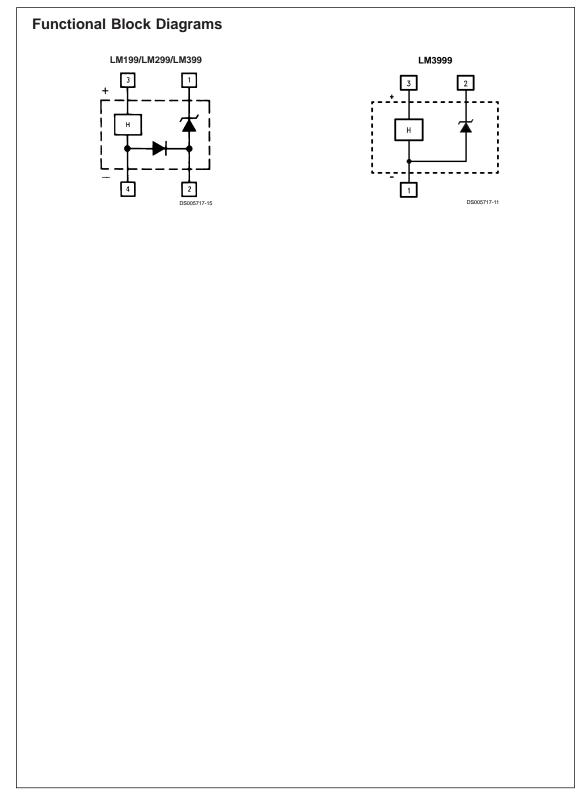
The LM3999 is packaged in a standard TO-92 package and is rated from 0°C to +70°C

Features

- Guaranteed 0.0001%/°C temperature coefficient
- Low dynamic impedance 0.5Ω
- Initial tolerance on breakdown voltage 2%
- Sharp breakdown at 400 µA
- Wide operating current 500 µA to 10 mA
- Wide supply range for temperature stabilizer
- Guaranteed low noise
- Low power for stabilization 300 mW at 25°C
- Long term stability 20 ppm
- Proven reliability, low-stress packaging in TO-46 integrated-circuit hermetic package, for low hysteresis after thermal cycling. 33 million hours MTBF at T_A = +25°C (T_J = +86°C)
- Certified long term stability available
- MIL-STD-883 compliant



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Absolute Maximum Ratings (Note 1)

Specifications for Military/Aerospace products are not contained in this datasheet. Refer to the following Reliability Electrical Test Specifications documents: RETS199X for LM199, RETS199AX for LM199A.

ability Electrical Test Specifications		LM
RETS199X for LM199, RETS199AX for LM1	99A.	LM
Temperature Stabilizer Voltage		LM
LM199/LM299/LM399	40V	Stora
LM3999	36V	Solde
Reverse Breakdown Current	20 mA	TO
Forward Current		TO
LM199/LM299/LM399	1 mA	
LM3999	–0.1 mA	

Reference to Substrate Voltage $V_{(RS)}$	(Note 2) 40	/
	-0.1	/
Operating Temperature Range		
LM199	-55°C to +125°C)
LM299	-25°C to +85°C)
LM399/LM3999	-0°C to +70°C)
Storage Temperature Range	–55°C to +150°C	2
Soldering Information		
TO-92 package (10 sec.)	+260°0	2
TO-46 package (10 sec.)	+300°C	2

Electrical Characteristics (Notes 3, 6)

Parameter	Parameter Conditions		L	LM199H/LM299H		LM399H			Units
			Min	Тур	Max	Min	Тур	Max	1
Reverse Breakdown Voltage	$0.5 \text{ mA} \le I_R \le 10 \text{ mA}$		6.8	6.95	7.1	6.6	6.95	7.3	V
Reverse Breakdown Voltage	$0.5 \text{ mA} \le I_R \le 10 \text{ mA}$			6	9		6	12	mV
Change with Current									
Reverse Dynamic Impedance	I _R = 1 mA			0.5	1		0.5	1.5	Ω
Reverse Breakdown	–55°C≤T _A ≤+85°C	LM199		0.00003	0.0001				%/°C
Temperature Coefficient	+85°C≤T _A ≤+125°C	LIVIT99		0.0005	0.0015				%/°C
	–25°C≤T _A ≤85°C	LM299		0.00003	0.0001				%/°C
	0°C≤T _A ≤+70°C	LM399					0.00003	0.0002	%/°C
RMS Noise	10 Hz ≤ f ≤ 10 kHz			7	20		7	50	μV
Long Term Stability	Stabilized, 22°C≤T _A ≤28	З°С,		20			20		ppm
	1000 Hours, I _R =1 mA±	⊧0.1%							
Temperature Stabilizer	T _A =25°C, Still Air, V _S =	:30V		8.5	14		8.5	15	mA
Supply Current	T _A =- 55°C			22	28				
Temperature Stabilizer			9		40	9		40	V
Supply Voltage									
Warm-Up Time to 0.05%	V _S = 30V, T _A = 25°C			3			3		sec.
Initial Turn-on Current	9≤V _S ≤40, T _A =+25°C, (Note 4)		140	200		140	200	mA

Note 1: "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits.

Electrical Characteristics (Note 3)

Parameter	Conditions		LM3999Z		Units	
		Min	Тур	Max		
Reverse Breakdown Voltage	$0.6 \text{ mA} \le I_R \le 10 \text{ mA}$	6.6	6.95	7.3	V	
Reverse Breakdown Voltage	$0.6 \text{ mA} \le I_R \le 10 \text{ mA}$		6	20	mV	
Change with Current						
Reverse Dynamic Impedance	I _R = 1 mA		0.6	2.2	Ω	
Reverse Breakdown	$0^{\circ}C \le T_{A} \le 70^{\circ}C$		0.0002	0.0005	%/°C	
Temperature Coefficient						
RMS Noise	10 Hz ≤ f ≤ 10 kHz		7		μV	
Long Term Stability	Stabilized, $22^{\circ}C \le T_A \le 28^{\circ}C$,		20		ppm	
	1000 Hours, I _R = 1 mA ±0.1%					
Temperature Stabilizer	$T_A = 25^{\circ}C$, Still Air, $V_S = 30V$		12	18	mA	
Temperature Stabilizer				36	V	
Supply Voltage						
Warm-Up Time to 0.05%	$V_{S} = 30V, T_{A} = 25^{\circ}C$		5		sec.	

Electrical Characteristics (Note 3) (Continued)					
Parameter Conditions LM3999Z					Units
		Min	Тур	Max	1
Initial Turn-On Current	$9 \le V_S \le 40, T_A = 25^{\circ}C$		140	200	mA
		·			

Electrical Characteristics (Notes 3, 6)

Parameter	Conditions		LM	1199AH, LI	//299AH		LM399A	н	Units
			Min	Тур	Max	Min	Тур	Мах	
Reverse Breakdown Voltage	$0.5 \text{ mA} \le I_R \le 10 \text{ mA}$		6.8	6.95	7.1	6.6	6.95	7.3	V
Reverse Breakdown Voltage	$0.5 \text{ mA} \le I_R \le 10 \text{ mA}$			6	9		6	12	mV
Change with Current									
Reverse Dynamic Impedance	I _R = 1 mA			0.5	1		0.5	1.5	Ω
Reverse Breakdown	–55°C≤T _A ≤+85°C			0.00002	0.00005				%/°C
Temperature Coefficient	+85°C≤T _A ≤+125°C	LM199A		0.0005	0.0010				%/°C
	–25°C≤T _A ≤85°C	LM299A		0.00002	0.00005				%/°C
	0°C≤T _A ≤+70°C	LM399A					0.00003	0.0001	%/°C
RMS Noise	10 Hz ≤ f ≤ 10 kHz			7	20		7	50	μV
Long Term Stability	Stabilized, 22°C≤T _A ≤28	°C,		20			20		ppm
	1000 Hours, I _R =1 mA±	0.1%							
Temperature Stabilizer	T _A =25°C, Still Air, V _S =3	30V		8.5	14		8.5	15	mA
Supply Current	T _A =- 55°C			22	28				
Temperature Stabilizer			9		40	9		40	V
Supply Voltage									
Warm-Up Time to 0.05%	V _S = 30V, T _A = 25°C			3			3		sec.
Initial Turn-on Current	9≤V _S ≤40, T _A =+25°C, (N	lote 4)		140	200		140	200	mA

Note 2: The substrate is electrically connected to the negative terminal of the temperature stabilizer. The voltage that can be applied to either terminal of the reference is 40V more positive or 0.1V more negative than the substrate.

Note 3: These specifications apply for 30V applied to the temperature stabilizer and $-55^{\circ}C \le T_A \le +125^{\circ}C$ for the LM199; $-25^{\circ}C \le T_A \le +85^{\circ}C$ for the LM299 and $0^{\circ}C \le T_A \le +70^{\circ}C$ for the LM399 and LM3999.

Note 4: This initial current can be reduced by adding an appropriate resistor and capacitor to the heater circuit. See the performance characteristic graphs to determine values.

Note 5: Do not wash the LM199 with its polysulfone thermal shield in TCE.

Note 6: A military RETS electrical test specification is available for the LM199H/883, LM199AH/883, and LM199AH-20/883 on request.

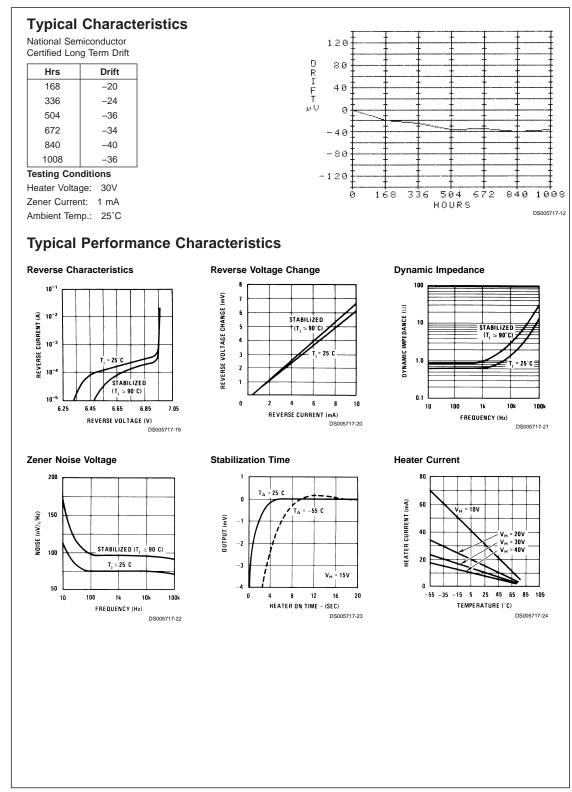
Ordering Information

Initial	0°C to +70°C	-25°C to +85°C	–55°C to +125°C	NS
Tolerance				Package
2%		LM299AH	LM199AH, LM199AH/883	H04D
5%	LM399H	LM299H		H04D
	LM399AH			
5%	LM3999Z			Z03A

Certified Long Term Drift

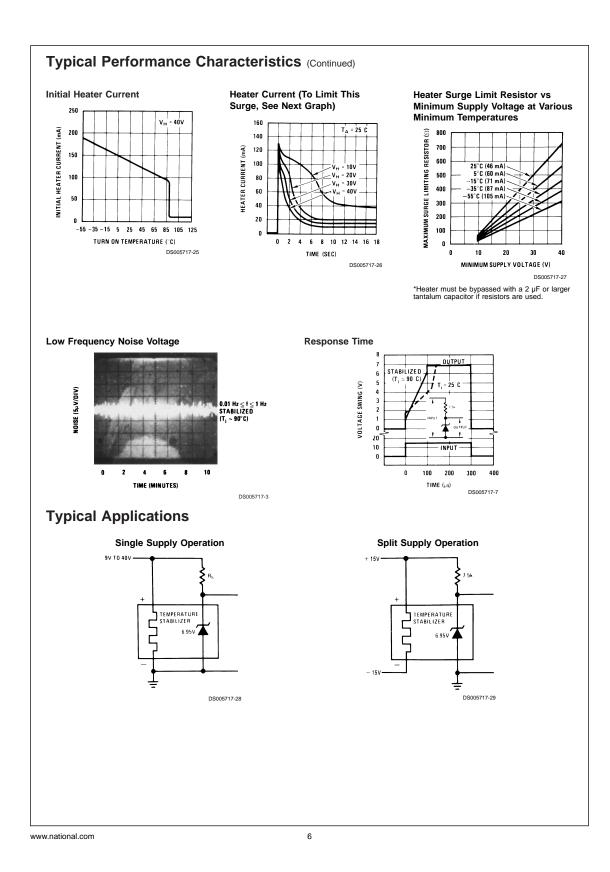
The National Semiconductor LM199AH-20, LM299AH-20, and LM399AH-50 are ultra-stable Zener references specially selected from the production runs of LM199AH, LM299AH, LM399AH and tested to confirm a long-term stability of 20, 20, or 50 ppm per 1000 hours, respectively. The devices are measured every 168 hours and the voltage of each device is logged and compared in such a way as to show the deviation from its initial value. Each measurement is taken with a probable-worst-case deviation of ±2 ppm, compared to the Reference Voltage, which is derived from several groups of NBS-traceable references such as LM199AH-20's, 1N827's,

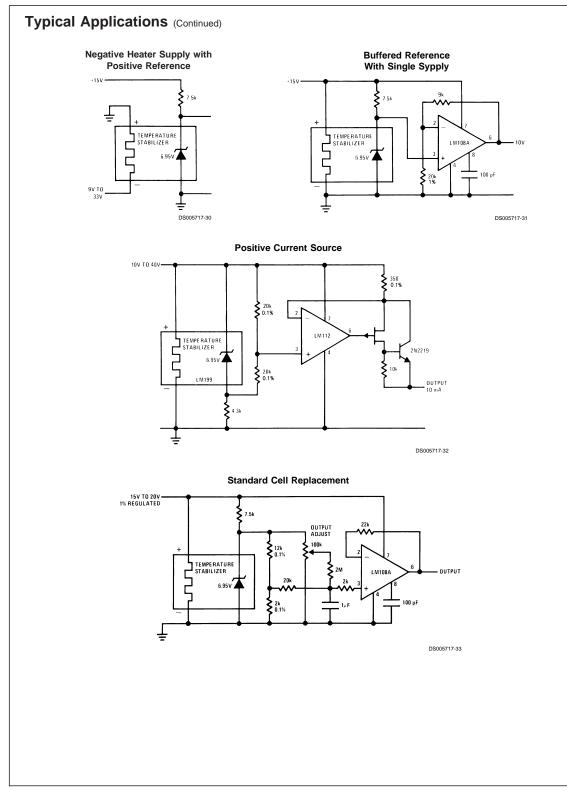
and saturated standard cells, so that the deviation of any one group will not cause false indications. Indeed, this comparison process has recently been automated using a specially prepared computer program which is custom-designed to reject noisy data (and require a repeat reading) and to record the average of the best 5 of 7 readings, just as a sagacious standards engineer will reject unbelievable readings. The typical characteristic for the LM199AH-20 is shown below. This computerized print-out form of each reference's stability is shipped with the unit.



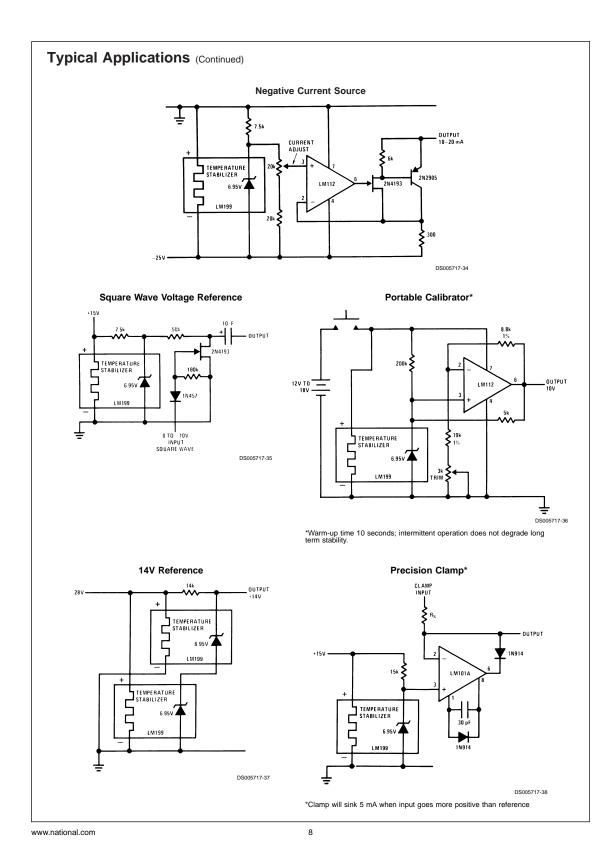
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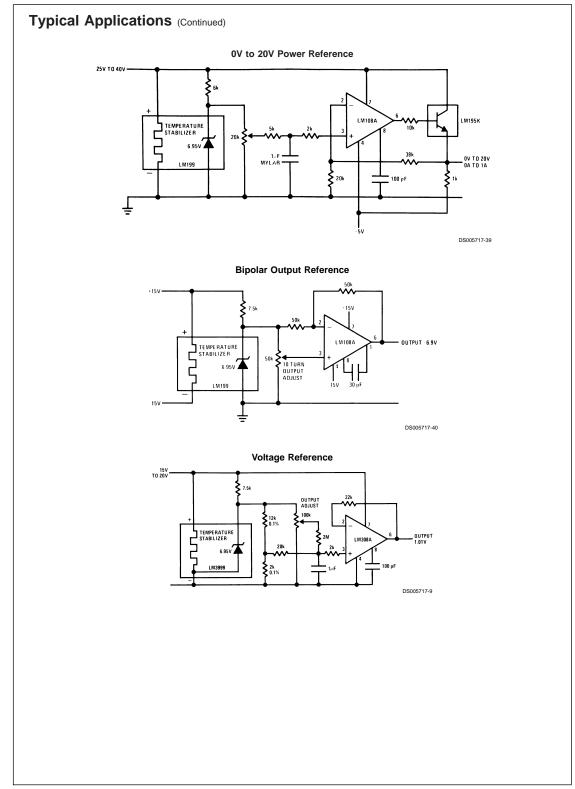
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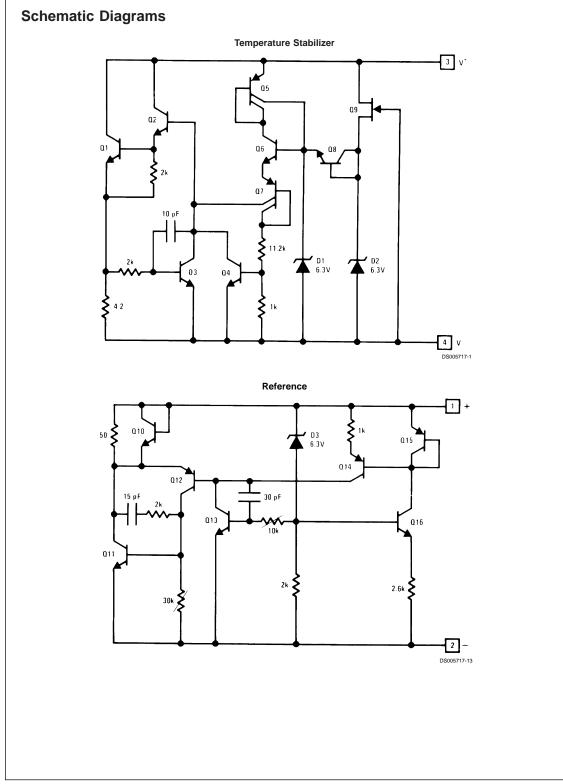




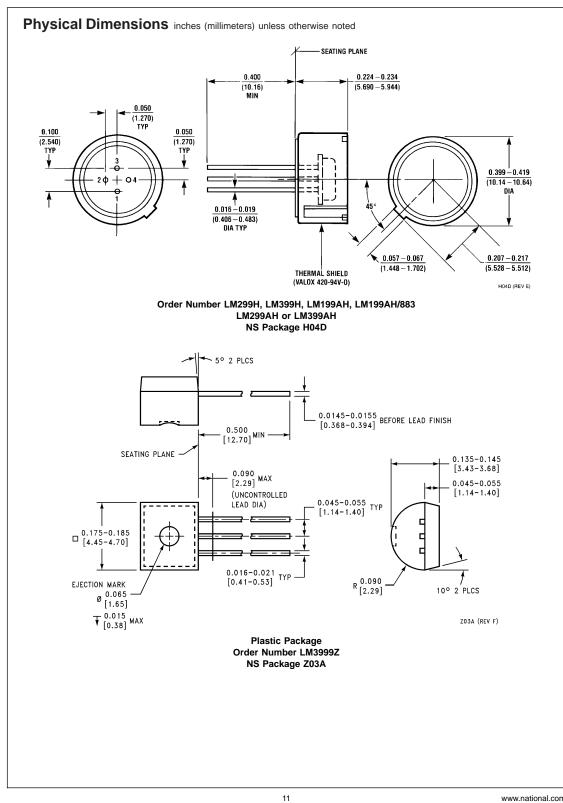
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Notes

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